PTO/SB/08A (10/01) (Substitute for form 1449A/PTO)	ATTY. DOCKET NO. COVA0003 DIV Client/Matter No. 90337.0006.001	APPLICATION NO. -------
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	FIRST NAMED INVENTOR Klaus Dimmler, Alfred P. Gnadinger	
(Use several sheets if necessary) Sheet __1___ of __5___	FILING DATE Herewith	ART UNIT

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	FIRST NAMED INVENTOR Klaus Dimmler, Alfred P. Gnadinger	
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	FIRST NAMED INVENTOR Klaus Dimmler, Alfred P. Gnadinger	
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	FIRST NAMED INVENTOR Klaus Dimmler, Alfred P. Gnadinger	
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary) Sheet ___5___ of ___5___	FIRST NAMED INVENTOR Klaus Dimmler, Alfred P. Gnadinger	
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EXAMINER SIGNATURE	Long Pham	DATE CONSIDERED	3/10/04

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